

SSCP005GN3

High Frequency High Gain PNP Power BJT

> Features

VCE	VBE	VCESAT Typ.	IC
-40V	-6V	-150mV	-3A

> Description

This device is produced with advanced high carrier density technology, which is especially used to minimize saturation voltage drop. This device particularly suits low voltage applications such as portable equipment, power management other battery powered circuits, and low in-line power dissipation are needed in a very small outline surface mount package. Excellent thermal and electrical capabilities.

Applications

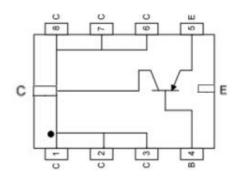
- Battery powered circuits
- Low in-line power dissipation circuits

> Ordering Information

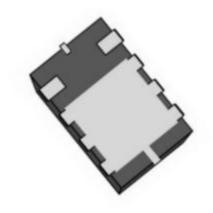
Device	Package	Shipping
SSCP005GN3	PDFN3X2-8L	3000/Reel

> Pin configuration

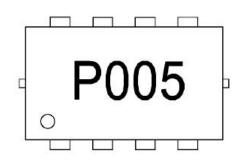
Top view



PDFN3X2-8L



Bottom view



Marking



➤ Absolute Maximum Ratings(T_A=25°C unless otherwise specified)

Symbol	Parameter	Ratings	Unit
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage -40		V
V _{EBO}	Emitter-Base Voltage	-6	V
ı	Collector Current@Note1	-3	Α
I _C	Collector Current@Note2	-2	A
Ісм	Pulsed Collector Current@Note3	-6	Α
D	Power Dissipation@Note1	3.0	W
P _D	Power Dissipation@Note2	1.5	VV
T _A	Operation Temperature Range	-40 to 85	°C
TL	Lead Temperature	260	°C
T _J ,T _{STG}	Operation and Storage temperature	-55 to 150	°C
	range		

> Thermal Resistance Ratings

Symbol	Parameter	Maximum	Unit	
D	Junction-to-Ambient Thermal	44		
$R_{\theta JA}$	Resistance@Note1	44	96 044	
Б	Junction-to-Ambient Thermal	85	°C/W	
R _{θJA}	Resistance@Note2			



➤ **Electronics Characteristics**(T_A=25°C unless otherwise specified)

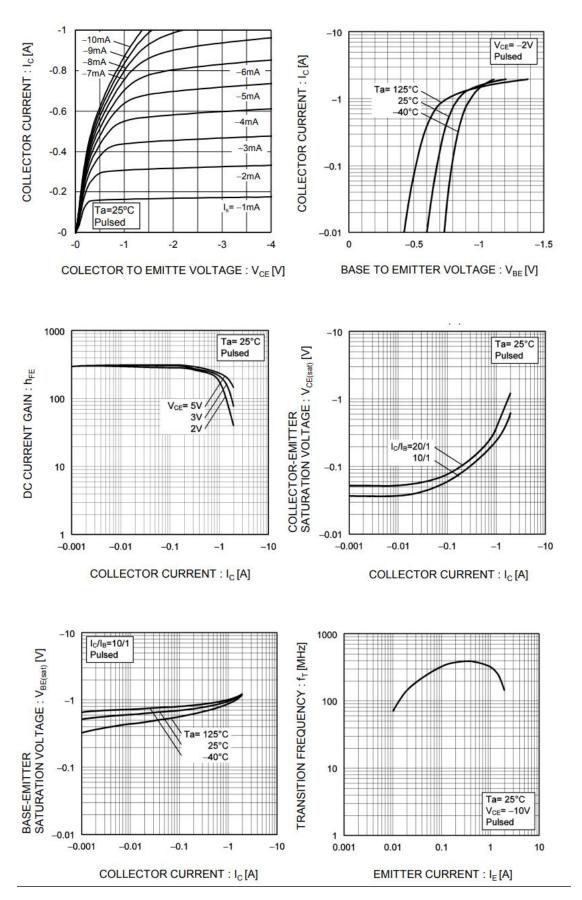
Symbol	Parameter	Test Conditions	Min	Тур.	Max	Unit
BVCBO	Collector-Base	IC=-50uA	-40			V
ВУСВО	Breakdown Voltage	IE=0	-40			V
BVCEO	Collector-Emitter	IC=-1mA	40	-40		V
BVCEO	Breakdown Voltage	IB=0	-40			V
BVEBO	Emitter-Base	IE=-1uA	-6			V
BVEBO	Breakdown Voltage	IC=0	-0			V
ICBO	Collector cut off	VCB=-20V			-0.1	uA
ЮВО	current	IE=0			-0.1	uA
IEBO	Emitter cut off	VEB=-4V			-0.1	uА
IEBO	current	IC=0			-0.1	uA
HFE	DC Current	VCE=-2V	100	200	350	
HFE	Gain@Note3	IC=-0.5A	100	200	350	
VCESAT	Collector-Emitter	IC=-1.5A			-0.2	V
VCESAI	Saturation Voltage	IB=-80mA			-0.2	V
VBESAT	Base-Emitter	IC=-1.5A			-1.2	V
VDESAI	Saturation Voltage	IB=-80mA			-1.2	V
f.	Transition frequency	VCE=-5V, IE=-0.1A	50	80		Hz
f _⊤		f=10MHz	50	00		□∠

Notes:

- Surface mounted on FR-4 Board using 1 square inch pad size, 1oz copper.
- 2. Surface mounted on FR-4 Board using minimum pad size, 1oz copper.
- 3. Pulse width=300us, Duty Cycle<2%.

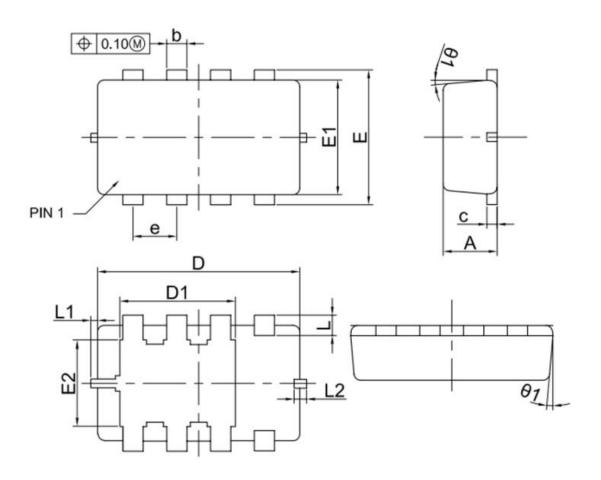


> Typical Performance Characteristics





Package Information



Combal		Dimensions in Millimeter	S
Symbol	Min.	Тур.	Max.
A	0.70	0.80	0.90
b	0.24	0.30	0.35
С	0.08	0.15	0.20
D	2.90	3.00	3.05
D1	1.52	1.62	1.72
E	1.90	2.00	2.10
E1	1.60	1.70	1.75
E2	1.07	1.17	1.27
е	0.65 BSC		
L	0.20	0.30	0.40
L1	0.00	-	0.10
L2	0.184MAX		
01	0°	5°	8°



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